SIEMENS

2M × 64-Bit Dynamic RAM EDO Module HYM 642005GS-50/-60

168 pin buffered DIMM module

Preliminary Information

- 168 pin JEDEC Standard, Buffered 8 Byte Dual In-Line Memory Module
- 1 bank 2M x 64 organisation
- Extended Data Out (EDO)
- Performance:

		-50	-60
tRAC	RAS Access Time	50 ns	60 ns
tCAC	CAS Access Time	18 ns	20 ns
tAA	Access Time from Address	30 ns	35 ns
tRC	Cycle Time	84 ns	104 ns
tHPC	EDO Mode Cycle Time	20 ns	25 ns

- Single + 5 V (± 10 %) supply
- $\overline{\text{CAS}}$-before-$\overline{\text{RAS}}$ refresh, $\overline{\text{RAS}}$-only-refresh
- Byte Write Capability
- Decoupling capacitors mounted on substrate
- All inputs, outputs and clock fully TTL compatible
- 4 Byte interleave enabled, Dual Address inputs (A0/B0)
- Buffered inputs except $\overline{\text{RAS}}$ and DQ
- Parallel Presence Detects
- Utilizes eight 2M × 8 -DRAMs in SOJ packages and four BiCMOS 8-bit buffers/line drivers 74ABT244
- 2048 refresh cycles / 32 ms
- Optimized for use in byte-write non-parity applications
- Gold contact pads, single sided module with 25.35 mm (1000 mil) height

The HYM 642005GS-50/-60 is a 16 MByte EDO-DRAM module organized as 2 097 152 words by 64-bit in a 168-pin, dual read-out, single-in-line package comprising four HYB 5117805BSJ 2M × 8 DRAMs in 400 mil wide SOJ packages mounted together with eight 0.2 µF ceramic decoupling capacitors on a PC board. All inputs except $\overline{RAS}$ and DQ are buffered by using four BiCMOS 8-bit buffers/line drivers.

Each HYB 5117805BSJ is described in the data sheet and is fully electrically tested and processed according to Siemens standard quality procedure prior to module assembly. After assembly onto the board, a further set of electrical tests is performed.

The density and speed of the module can be detected by the use of presence detect pins.

Ordering Information

Type	Ordering Code	Package	Descriptions
HYM 642005GS-50		L-DIM-168-20	50 ns DRAM module
HYM 642005GS-60		L-DIM-168-20	60 ns DRAM module

Pin Names

A0-A10,B0	Address Input
DQ0 - DQ63	Data Input/Output
RAS0, RAS2	Row Address Strobe
CAS0 - CAS7	Column Address Strobe
WE0, WE2	Read / Write Input
OE0, OE2	Output Enable
Vcc	Power (+5 Volt)
Vss	Ground
PD1 - PD8	Presence Detect Pins
PDE	Presence Detect Enable
ID0 , ID1	ID indentification bit
N.C.	No Connection

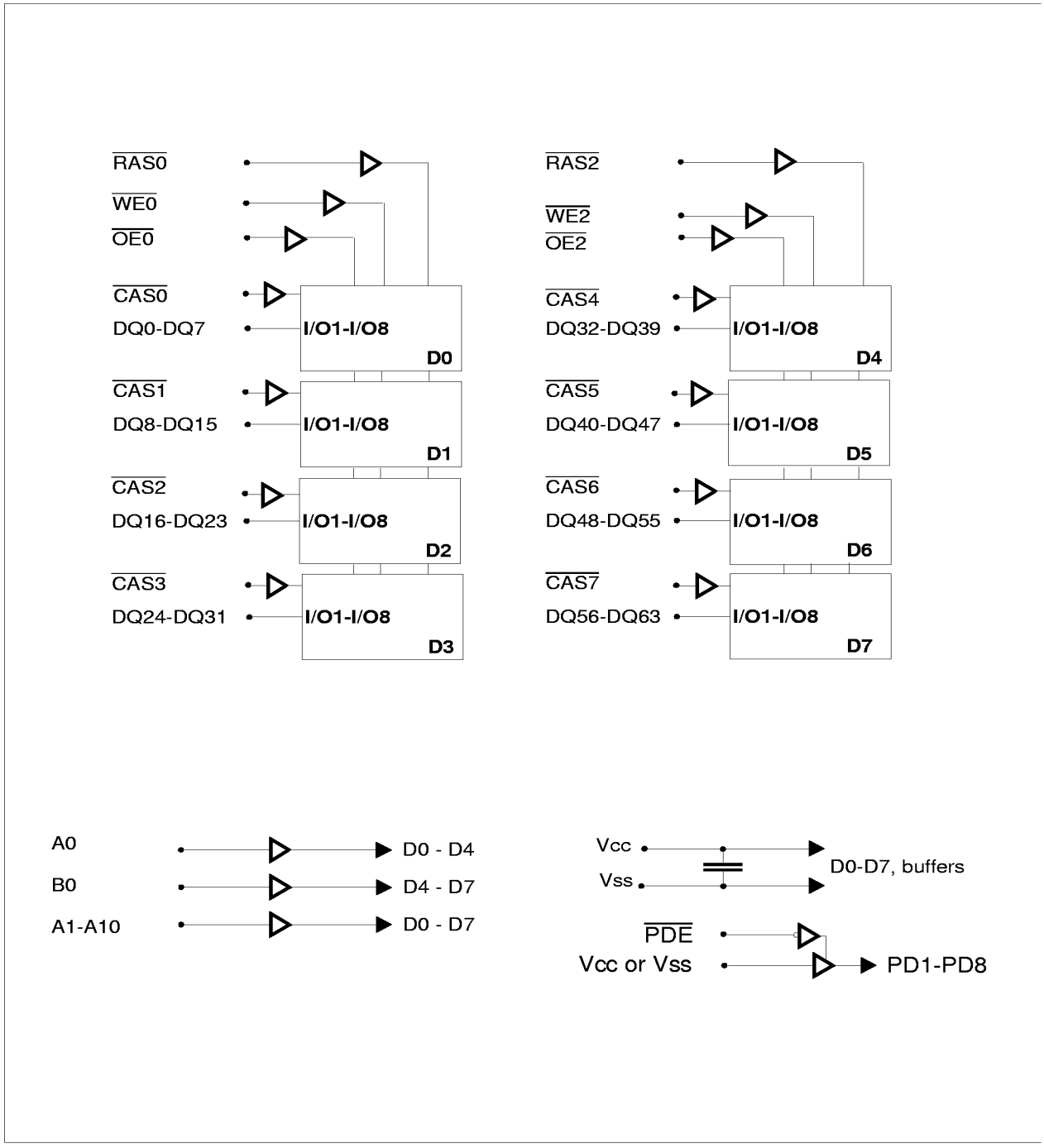
Presence-Detect and ID-pin Truth Table:

Module	ID0	ID1	PD1	PD2	PD3	PD4	PD5	PD6	PD7	PD8
HYM 642005GS-50	Vss	Vss	1	0	0	1	1	0	0	1
HYM 642005GS-60	Vss	Vss	1	0	0	1	1	1	1	1

Note: 1 = high level (driver output), 0 = low level (driver output) for $\overline{PDE}$ active (ground) . For $\overline{PDE}$ at a high level all PD terminals are in tri-state.

Pin Configuration

PIN #	Symbol	PIN #	Symbol		PIN #	Symbol	PIN #	Symbol
1	VSS	43	VSS		85	VSS	127	VSS
2	DQ0	44	OE2		86	DQ32	128	NC
3	DQ1	45	RAS2		87	DQ33	129	NC
4	DQ2	46	CAS4		88	DQ34	130	CAS5
5	DQ3	47	CAS6		89	DQ35	131	CAS7
6	VCC	48	WE2		90	VCC	132	PDE
7	DQ4	49	VCC		91	DQ36	133	VCC
8	DQ5	50	NC		92	DQ37	134	NC
9	DQ6	51	NC		93	DQ38	135	NC
10	DQ7	52	DQ16		94	DQ39	136	DQ48
11	NC	53	DQ17		95	NC	137	DQ49
12	VSS	54	VSS		96	VSS	138	VSS
13	DQ8	55	DQ18		97	DQ40	139	DQ50
14	DQ9	56	DQ19		98	DQ41	140	DQ51
15	DQ10	57	DQ20		99	DQ42	141	DQ52
16	DQ11	58	DQ21		100	DQ43	142	DQ53
17	DQ12	59	VCC		101	DQ44	143	VCC
18	VCC	60	DQ22		102	VCC	144	DQ54
19	DQ13	61	NC		103	DQ45	145	NC
20	DQ14	62	NC		104	DQ46	146	NC
21	DQ15	63	NC		105	DQ47	147	NC
22	NC	64	NC		106	NC	148	NC
23	VSS	65	DQ23		107	VSS	149	DQ55
24	NC	66	NC		108	NC	150	NC
25	NC	67	DQ24		109	NC	151	DQ55
26	VCC	68	VSS		110	VCC	152	VSS
27	WE0	69	DQ25		111	NC	153	DQ57
28	CAS0	70	DQ26		112	CAS1	154	DQ58
29	CAS2	71	DQ27		113	CAS3	155	DQ59
30	RAS0	72	DQ28		114	NC	156	DQ60
31	OE0	73	VCC		115	NC	157	VCC
32	VSS	74	DQ29		116	VSS	158	DQ61
33	A0	75	DQ30		117	A1	159	DQ62
34	A2	76	DQ31		118	A3	160	DQ63
35	A4	77	NC		119	A5	161	NC
36	A6	78	VSS		120	A7	162	VSS
37	A8	79	PD1		121	A9	163	PD2
38	A10	80	PD3		122	NC	164	PD4
39	NC	81	PD5		123	NC	165	PD6
40	VCC	82	PD7		124	VCC	166	PD8
41	NC	83	ID0		125	NC	167	ID1
42	NC	84	VCC		126	B0	168	VCC



Block Diagram

Absolute Maximum Ratings

Operating temperature range ..... 0 to + 70 °C
Storage temperature range..... – 55 to + 125 °C
Input/output voltage ..... – 1 to + 7 V
Power supply voltage..... – 1 to + 7 V
Power dissipation..... 6,72 W
Data out current (short circuit) ..... 50 mA

Note: *Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

DC Characteristics

T_A = 0 to 70 °C; V_{CC} = 5 V ± 10 %

Parameter	Symbol	Limit Values		Unit	Test Condition
		min.	max.		
Input high voltage	V_{IH}	2.4	Vcc+0.5	V	1)
Input low voltage	V_{IL}	– 1.0	0.8	V	1)
Output high voltage (I_{OUT} = – 5 mA)	V_{OH}	2.4	–	V	1)
Output low voltage (I_{OUT} = 4.2 mA)	V_{OL}	–	0.4	V	1)
Input leakage current (0 V < V_{IN} < 6.5 V, all other pins = 0 V)	$I_{I(L)}$	– 10	10	µA	1)
Output leakage current (DO is disabled, 0 V < V_{OUT} < 5.5 V)	$I_{O(L)}$	– 10	10	µA	1)
Average V_{CC} supply current:	I_{CC1}				2) 3) 4)
-50 version		–	1010	mA	
-60 version		–	930	mA	
($\overline{RAS}$, $\overline{CAS}$, address cycling, t_{RC} = t_{RC} min.)					
Standby V_{CC} supply current ($\overline{RAS}$ = $\overline{CAS}$ = V_{IH})	I_{CC2}	–	50	mA	–
Average V_{CC} supply current during $\overline{RAS}$ only refresh cycles:	I_{CC3}				2) 4)
-50 version		–	1010	mA	
-60 version		–	930	mA	
($\overline{RAS}$ cycling, $\overline{CAS}$ = V_{IH}, t_{RC} = t_{RC} min.)					

DC Characteristics (cont'd) [1]

Parameter	Symbol	Limit Values		Unit	Test Condition
		min.	max.		
Average V_{CC} supply current during hyper page mode (EDO) :	I_{CC4}				
-50 version		–	610	mA	2) 3) 4)
-60 version		–	490	mA	
		–			
($\overline{RAS}$ = V_{IL}, $\overline{CAS}$, address cycling t_{PC} = t_{PC} min.)					
Standby V_{CC} supply current ($\overline{RAS}$ = $\overline{CAS}$ = V_{CC} – 0.2 V)	I_{CC5}	–	30	mA	–
Average V_{CC} supply current during $\overline{CAS}$-before-$\overline{RAS}$ refresh mode:	I_{CC6}				
-50 version		–	1010	mA	2) 4)
-60 version		–	930	mA	
($\overline{RAS}$, $\overline{CAS}$ cycling, t_{RC} = t_{RC} min.)					

Capacitance
T_A = 0 to 70 °C; V_{CC} = 5 V ± 10 %; f = 1 MHz

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Input capacitance (A0 to A9,B0)	C_{I1}	–	10	pF
Input capacitance ($\overline{RAS0}$, $\overline{RAS2}$)	C_{I2}	–	42	pF
Input capacitance ($\overline{CAS0}$-$\overline{CAS7}$)	C_{I3}	–	15	pF
Input capacitance ($\overline{WE0}$,$\overline{WE2}$,$\overline{OE0}$,$\overline{OE2}$)	C_{I4}	–	15	pF
I/O capacitance (DQ0-DQ63)	C_{IO1}	–	15	pF

AC Characteristics (note: 5,6,7,8)
T_A = 0 to 70 °C, V_{CC} = 5.0 ± 10 %

Parameter	Symbol	-50		-60		Unit	Note
		min.	max.	min.	max.		
common parameters							
Random read or write cycle time	t_{RC}	84	–	104	–	ns	
RAS precharge time	t_{RP}	30	–	40	–	ns	
RAS pulse width	t_{RAS}	50	100k	60	100k	ns	
$\overline{CAS}$ pulse width	t_{CAS}	8	10k	10	10k	ns	
Row address setup time	t_{ASR}	5	–	5	–	ns	9
Row address hold time	t_{RAH}	6	–	8	–	ns	10
Column address setup time	t_{ASC}	2	–	2	–	ns	11
Column address hold time	t_{CAH}	13	–	15	–	ns	9
$\overline{RAS}$ to $\overline{CAS}$ delay time	t_{RCD}	10	32	12	40		12
$\overline{RAS}$ to column address delay time	t_{RAD}	8	20	10	25	ns	12
$\overline{RAS}$ hold time	t_{RSH}	18	–	20	–	ns	9
$\overline{CAS}$ hold time	t_{CSH}	38	–	48	–	ns	10
$\overline{CAS}$ to $\overline{RAS}$ precharge time	t_{CRP}	10	–	10	–	ns	9
Transition time (rise and fall)	t_T	1	30	1	30	ns	7
Refresh period	t_{REF}	–	32	–	32	ms	
Read Cycle							
Access time from $\overline{RAS}$	t_{RAC}	–	50	–	60	ns	13,14
Access time from $\overline{CAS}$	t_{CAC}	–	18	–	20	ns	9,13,14
Access time from column address	t_{AA}	–	30	–	35	ns	9,13, 15
$\overline{OE}$ access time	t_{OEA}	–	18	–	20	ns	9,13
Column address to $\overline{RAS}$ lead time	t_{RAL}	30	–	35	–	ns	9
Read command setup time	t_{RCS}	2	–	2	–	ns	11
Read command hold time	t_{RCH}	2	–	2	–	ns	11,16
Read command hold time referenced to $\overline{RAS}$	t_{RRH}	0	–	0	–	ns	16
$\overline{CAS}$ to output in low-Z	t_{CLZ}	2	–	2	–	ns	11,13
Output buffer turn-off delay	t_{OFF}	–	18	–	20	ns	9,17
Output buffer turn-off delay from $\overline{OE}$	t_{OEZ}	–	18	–	20	ns	9,17

AC Characteristics (cont'd)(note: 5,6,7,8)
T_A = 0 to 70 °C, V_{CC} = 5.0 ± 10 %

Parameter	Symbol	-50		-60		Unit	Note
		min.	max.	min.	max.		
$\overline{CAS}$ delay time from Din	t_{DZC}	0	–	0	–	ns	18
Data to $\overline{OE}$ low delay	t_{DZO}	0	–	0	–	ns	18
$\overline{CAS}$ high to data delay	t_{CDD}	15	–	18	–	ns	9,19
$\overline{OE}$ high to data delay	t_{ODD}	15	–	18	–	ns	9,19
Write Cycle							
Write command hold time	t_{WCH}	13	–	15	–	ns	9
Write command pulse width	t_{WP}	8	–	10	–	ns	
Write command setup time	t_{WCS}	2	–	2	–	ns	11,20
Write command to $\overline{RAS}$ lead time	t_{RWL}	18	–	20	–	ns	9
Write command to $\overline{CAS}$ lead time	t_{CWL}	13	–	15	–	ns	
Data setup time	t_{DS}	-2	–	-2	–	ns	10,21
Data hold time	t_{DH}	13	–	15	–	ns	9,21
Read-Modify-Write Cycle							
Read-write cycle time	t_{RWC}	118	–	143	–	ns	9
$\overline{RAS}$ to $\overline{WE}$ delay time	t_{RWD}	66	–	77	–	ns	11,21
$\overline{CAS}$ to $\overline{WE}$ delay time	t_{CWD}	29	–	34	–	ns	11,21
Column address to $\overline{WE}$ delay time	t_{AWD}	41	–	49	–	ns	11,21
$\overline{OE}$ command hold time	t_{OEH}	8	–	11	–	ns	10
Hyper Page Mode (EDO) Cycle							
Hyper page mode cycle time	t_{PC}	20	–	25	–	ns	
$\overline{CAS}$ precharge time	t_{CP}	8	–	10	–	ns	
Access time from $\overline{CAS}$ precharge	t_{CPA}	–	32	–	37	ns	9,13
Output data hold time	t_{COH}	3	–	3	–	ns	10
$\overline{RAS}$ pulse width	t_{RAS}	50	200k	60	200k	ns	
$\overline{CAS}$ precharge to $\overline{RAS}$ Delay	t_{RHCP}	32	–	37	–	ns	9

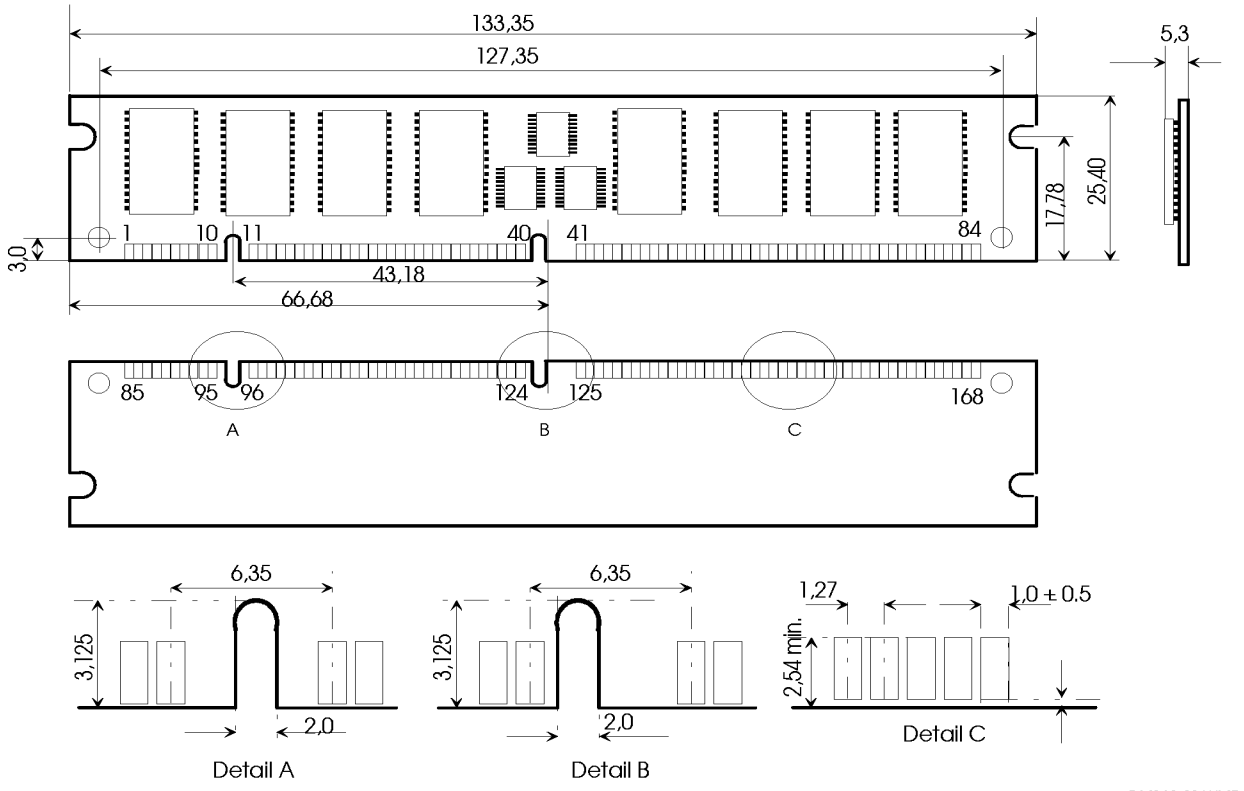
AC Characteristics (cont'd)(note: 5,6,7,8)
T_A = 0 to 70 °C, V_{CC} = 5.0 ± 10 %

Parameter	Symbol	-50		-60		Unit	Note
		min.	max.	min.	max.		
Hyper Page Mode Read-Modify-Write Cycle							
Hyper page mode read-write cycle time	t_{PRWC}	60	–	70	–	ns	11
$\overline{CAS}$ precharge to $\overline{WE}$	t_{CPWD}	43	–	51	–	ns	11,21
$\overline{CAS}$-before-$\overline{RAS}$ Refresh Cycle							
$\overline{CAS}$ setup time	t_{CSR}	12	–	12	–	ns	11
$\overline{CAS}$ hold time	t_{CHR}	8	–	8	–	ns	10
$\overline{RAS}$ to $\overline{CAS}$ precharge time	t_{RPC}	5	–	5	–	ns	
Write to $\overline{RAS}$ precharge time	t_{WRP}	12	–	12	–	ns	11
Write hold time referenced to $\overline{RAS}$	t_{WRH}	8	–	8	–	ns	10
Presence Detect Read Cycle							
$\overline{PDE}$ to valid presence detect data	t_{PD}	–	10	–	10	ns	
$\overline{PDE}$ inactive to presence detects inactive	t_{PDOFF}	0	10	0	10	ns	

Notes:

1) All voltages are referenced to VSS.
2) ICC1, ICC3, ICC4 and ICC6 depend on cycle rate.
3) ICC1 and ICC4 depend on output loading. Specified values are measured with the output open.
4) Address can be changed once or less while $\overline{RAS}$ = Vil.In the case of ICC4 it can be changed once or less during a hyper page mode (EDO) cycle (thpc).
5) An initial pause of 100 µs is required after power-up followed by 8 RAS-only-refresh cycles, before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 $\overline{CAS}$-before-$\overline{RAS}$ initialization cycles instead of 8 $\overline{RAS}$ cycles are required.
6) AC measurements assume tT = 2 ns.
7) VIH (min.) and VIL (max.) are reference levels for measuring timing of input signals. Also, transition times are measured between VIH and VIL.
8) The specified timings include buffer, loading and skew delay adders: 2ns minimum, 5ns ($\overline{CAS}$, $\overline{WE}$, $\overline{OE}$, addresses) maximum delay, no pulse shrinkage to the DRAM device timings. The data and RAS signals are not buffered, which preserves the DRAMs access specification of 50ns and 60ns.
9) A +5ns timing skew from the DRAM to the module resulted from the addition of line drivers.
10) A -2ns timing skew from the DRAM to the module resulted from the addition of line drivers.
11) A +2ns timing skew from the DRAM to the module resulted from the addition of line drivers.
12) A -2ns (min.) and a -5ns (max.) timing skew from the DRAM to the module resulted from the addition of line drivers.
13) Measured with the specified current load and 100 pF at Voh = 2.4 V and Vol = 0.4 V. Access time is determined by the latter of tRAC, tCAC, tAA, tCPA, tOEA. tCAC is measured from tristate.
14) Operation within the tRCD (max.) limit ensures that tRAC (max.) can be met. tRCD (max.) is specified as a reference point only: If tRCD is greater than the specified tRCD (max.) limit, then access time is controlled by tCAC.
15) Operation within the tRAD (max.) limit ensures that tRAC (max.) can be met. tRAD (max.) is specified as a reference point only: If tRAD is greater than the specified tRAD (max.) limit, then access time is controlled by tAA.
16) Either tRCH or tRRH must be satisfied for a read cycle.
17) tOFF (max.) and tOEZ (max.) define the time at which the outputs achieve the open-circuit condition and are not referenced to output voltage levels. tOFF is referenced from the rising edge of $\overline{RAS}$ or $\overline{CAS}$, whichever occurs last.
18) Either tDZC or tDZO must be satisfied.
19) Either tCDD or tODD must be satisfied.
20) tWCS, tRWD, tCWD, tAWD and tCPWD are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If tWCS > tWCS (min.), the cycle is an early write cycle and the I/O pin will remain open-circuit (high impedance) through the entire cycle; if tRWD > tRWD (min.), tCWD > tCWD (min.), tAWD > tAWD (min.) and tCPWD > tCPWD (min.) , the cycle is a read-write cycle and I/O pins will contain data read from the selected cells. If neither of the above sets of conditions is satisfied, the condition of the I/O pins (at access time) is indeterminate.
21) These parameters are referenced to $\overline{CAS}$ leading edge in early write cycles and to $\overline{WE}$ leading edge in Read-Modify-Write cycles.

L-DIM-168-20
Module package
(dual read-out, single in-line memory module)



preliminary drawing